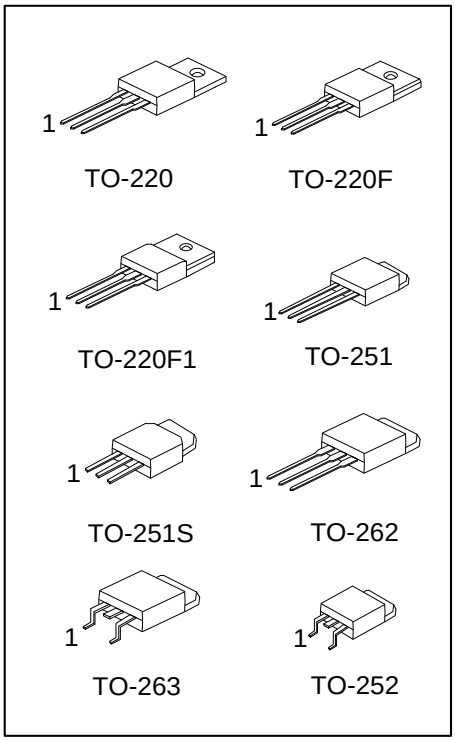
10NM65-U2

Power MOSFET

10A, 650V N-CHANNEL SUPER-JUNCTION MOSFET



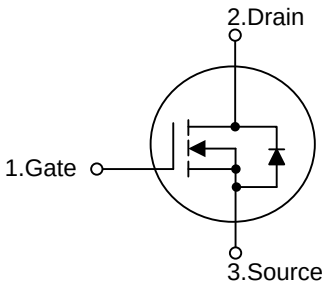
■ DESCRIPTION

The **UTC 10NM65-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)} \leq 0.58\Omega$ @ V_{GS}=10V, I_D=5.0A
* By using Super Junction Structure
* Fast Switching
* With 100% Avalanche Tested

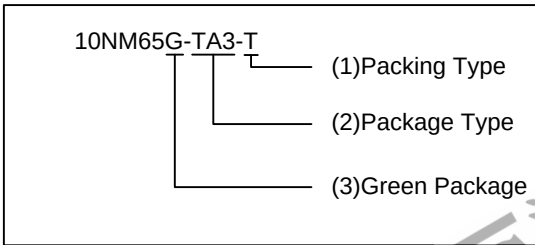
■ SYMBOL



■ ORDERING INFORMATION

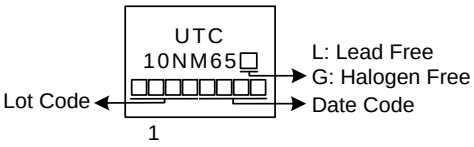
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10NM65L-TA3-T	10NM65G-TA3-T	TO-220	G	D	S	Tube
10NM65L-TF3-T	10NM65G-TF3-T	TO-220F	G	D	S	Tube
10NM65L-TF1-T	10NM65G-TF1-T	TO-220F1	G	D	S	Tube
10NM65L-TM3-T	10NM65G-TM3-T	TO-251	G	D	S	Tube
10NM65L-TMS-T	10NM65G-TMS-T	TO-251S	G	D	S	Tube
10NM65L-TN3-R	10NM65G-TN3-R	TO-252	G	D	S	Tape Reel
10NM65L-T2Q-T	10NM65G-T2Q-T	TO-262	G	D	S	Tube
10NM65L-TQ2-T	10NM65G-TQ2-T	TO-263	G	D	S	Tube
10NM65L-TQ2-R	10NM65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F
TM3: TO-251, TMS: TO-251S, TN3: TO-252,
T2Q: TO-262, TQ2: TO-263
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	10	A
	Pulsed (Note 2)	I_{DM}	20	A
Avalanche Current (Note 2)		I_{AR}	1.9	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	312	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	5.6	V/ns
Power Dissipation	TO-220/TO-262/TO-263	P_D	78	W
	TO-220F/TO-220F1		25	W
	TO-251/TO-251S TO-252		52	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=100mH, I_{AS}=2.5A, V_{DD}= 50V, R_G=25Ω, Starting T_J=25°C
4. I_{SD} ≤10A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-262 TO-263	θ_{JA}	62.5	°C/W
	TO-251/TO-251S TO-252		110	
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	1.6	°C/W
	TO-220F/TO-220F1		5.0	
	TO-251/TO-251S TO-252		2.4 (Note)	

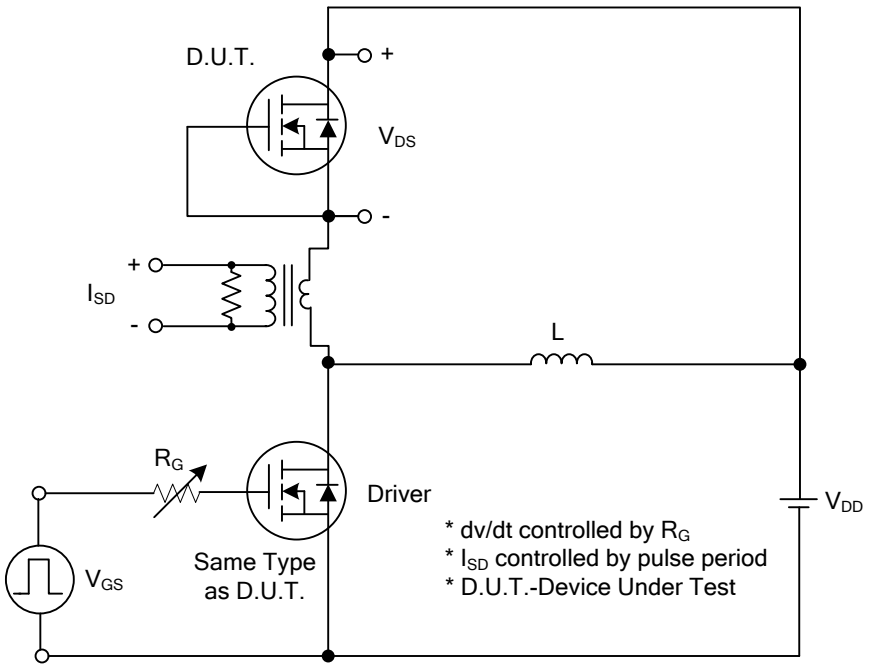
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

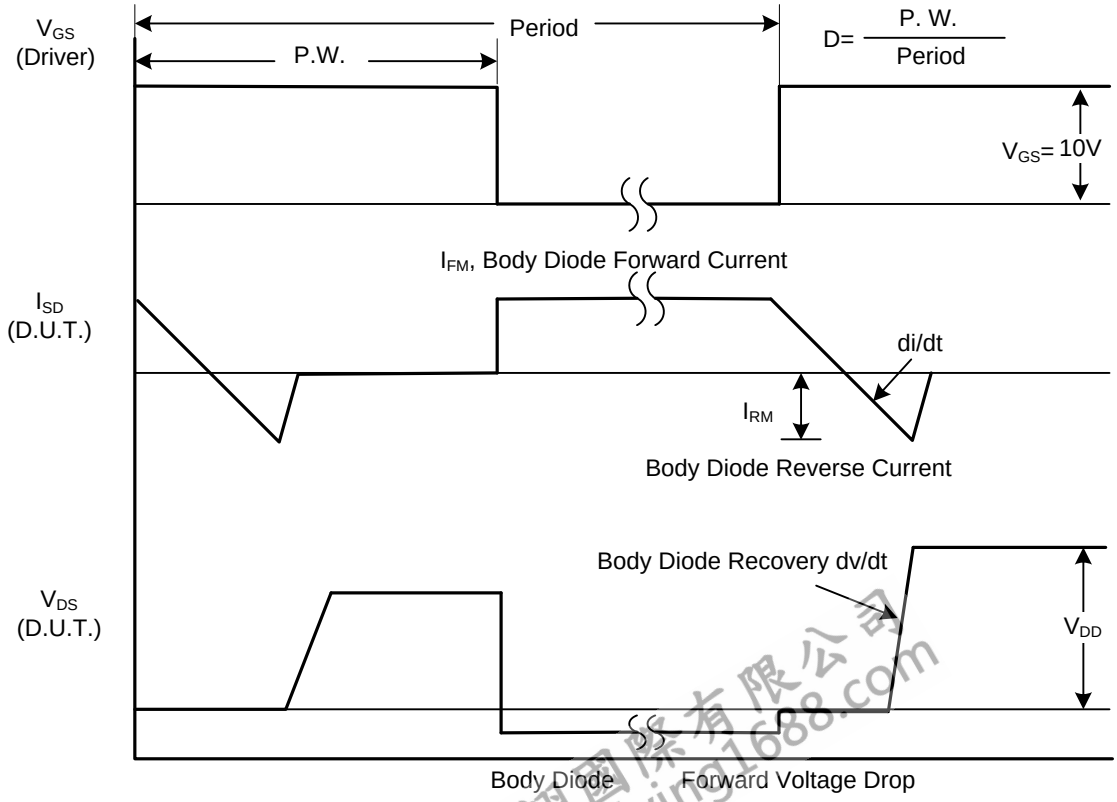
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{DS}=0V ,V_{GS}=30V			100	nA
	Reverse		V_{DS}=0V ,V_{GS}=-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}= V_{GS}, I_D=250μA	2.5		4.5	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=5.0A			0.58	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		610		pF
Output Capacitance		C_{OSS}			500		pF
Reverse Transfer Capacitance		C_{RSS}			40		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=520V, V_{GS}=10V, I_D=10A, I_G=1mA (Note 1, 2)		27		nC
Gate to Source Charge		Q_{GS}			9.2		nC
Gate to Drain Charge		Q_{GD}			7.5		nC
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=10A, R_G=25Ω (Note 1, 2)		8		ns
Rise Time		t_R			21		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			63		ns
Fall-Time		t_F			36		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				10	A
Maximum Body-Diode Pulsed Current		I_{SM}				20	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S =10A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S =10A, V_{GS}=0V, dI_F/dt=100A/μs		380		ns
Body Diode Reverse Recovery Charge		Q_{rr}			5		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

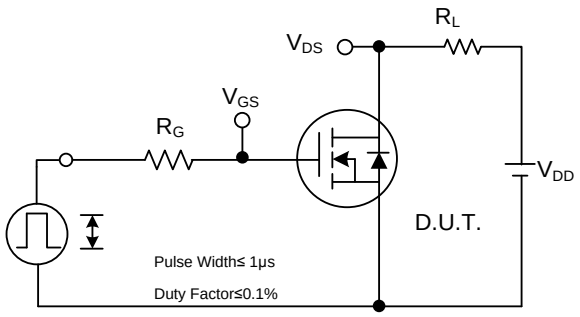


Peak Diode Recovery dv/dt Test Circuit

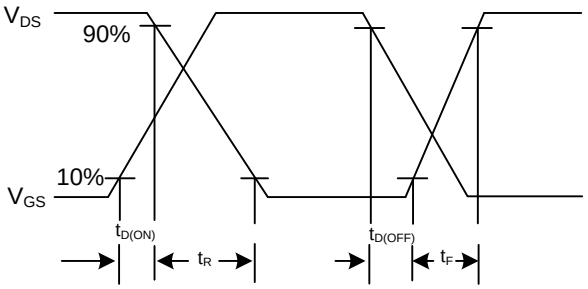


Peak Diode Recovery dv/dt Waveforms

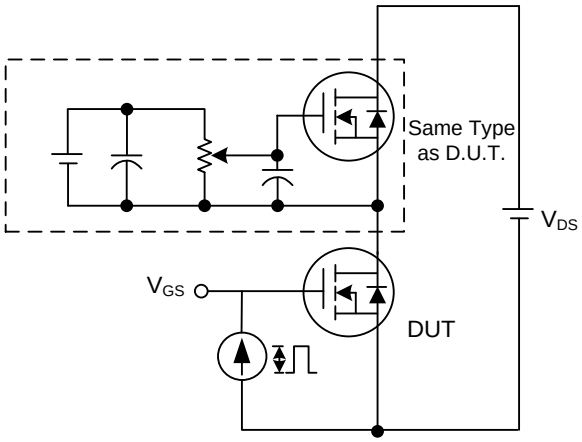
■ TEST CIRCUITS AND WAVEFORMS



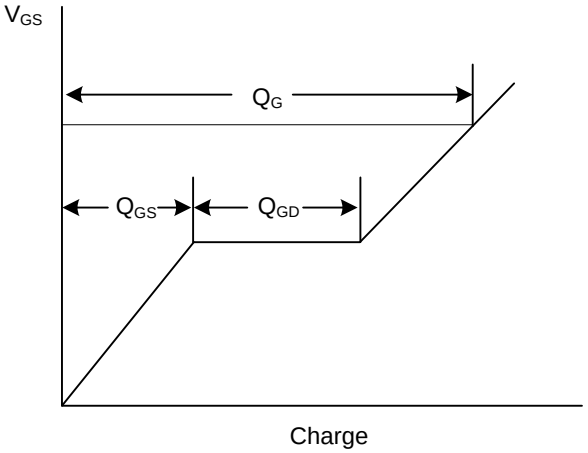
Switching Test Circuit



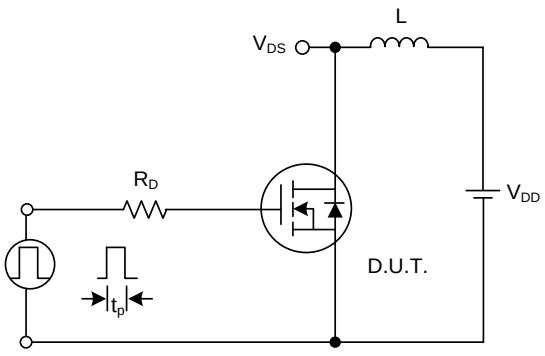
Switching Waveforms



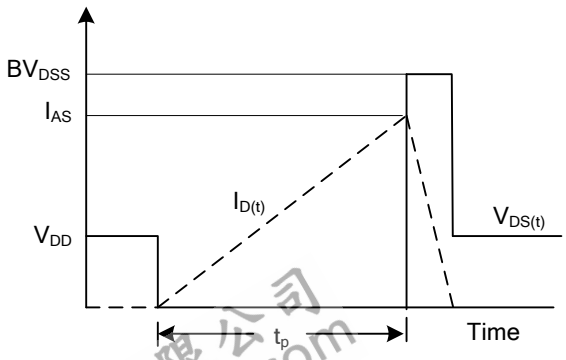
Gate Charge Test Circuit



Gate Charge Waveform



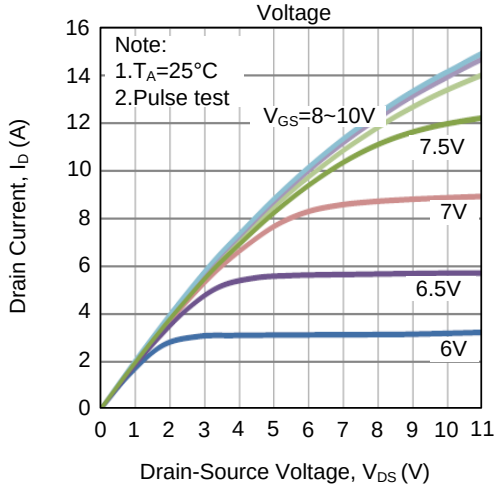
Unclamped Inductive Switching Test Circuit



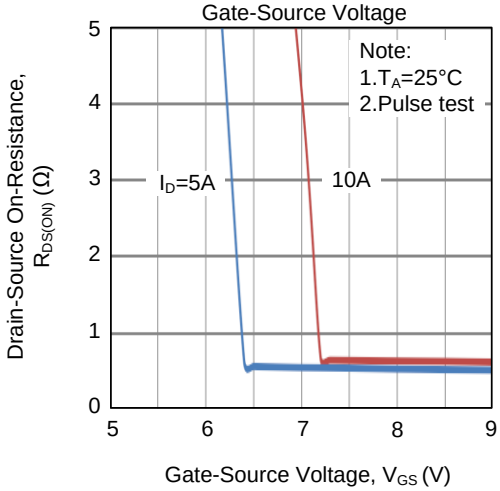
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

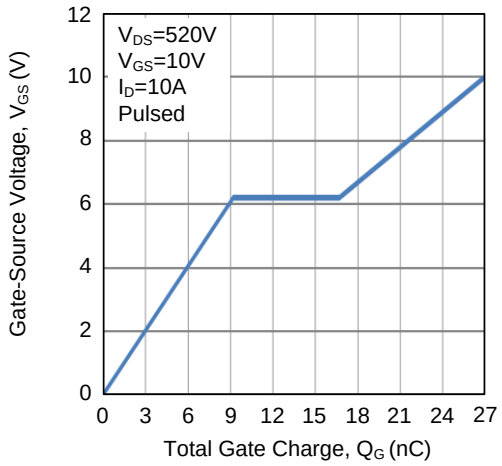
Drain Current vs. Drain-Source Voltage



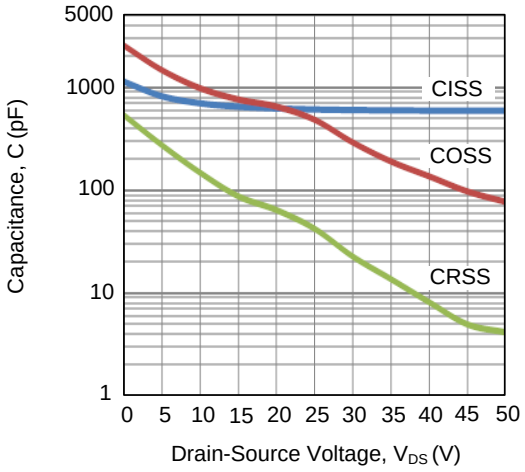
Drain-Source On-Resistance vs. Gate-Source Voltage



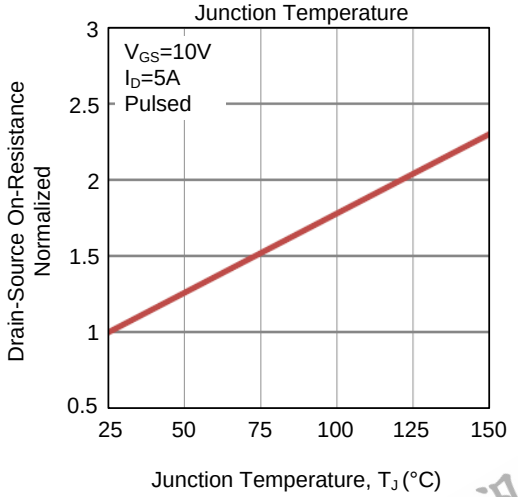
Gate Charge Characteristics



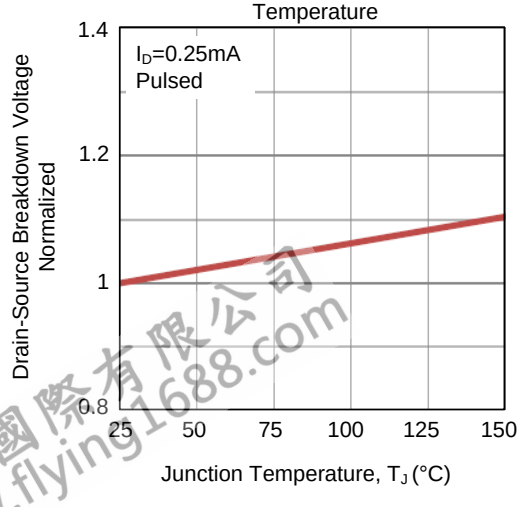
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

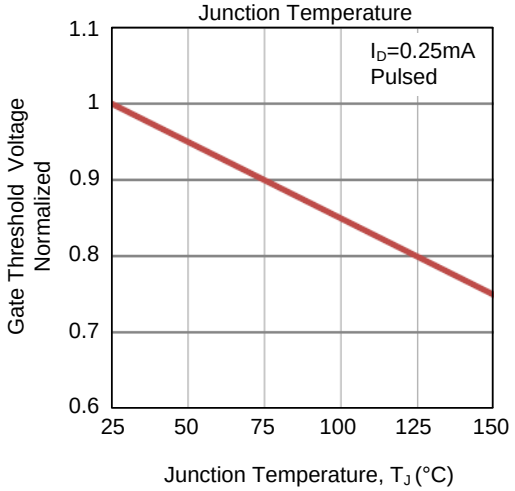


Breakdown Voltage vs. Junction Temperature

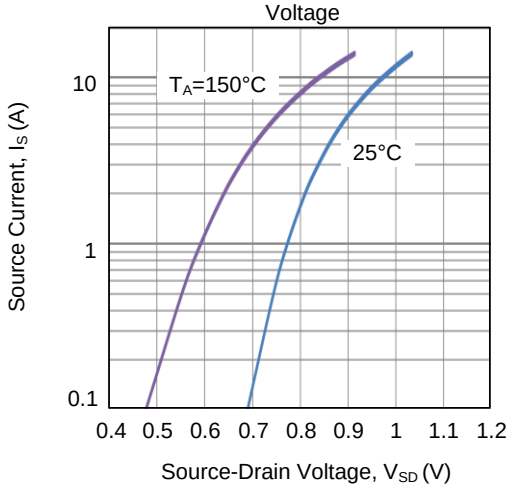


■ TYPICAL CHARACTERISTICS

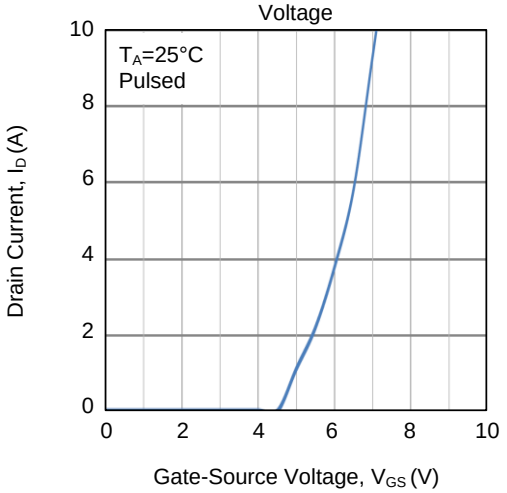
Gate Threshold Voltage vs. Junction Temperature



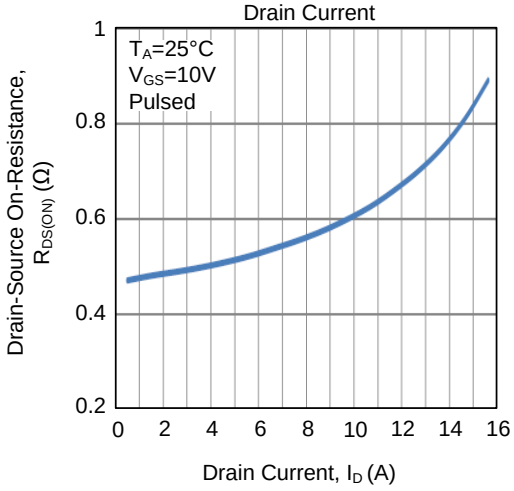
Source Current vs. Source-Drain Voltage



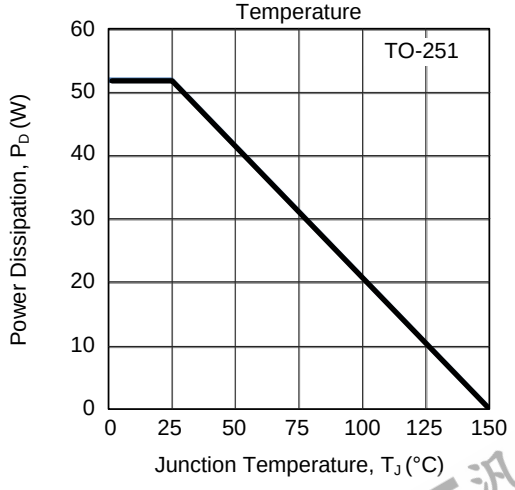
Drain Current vs. Gate-Source Voltage



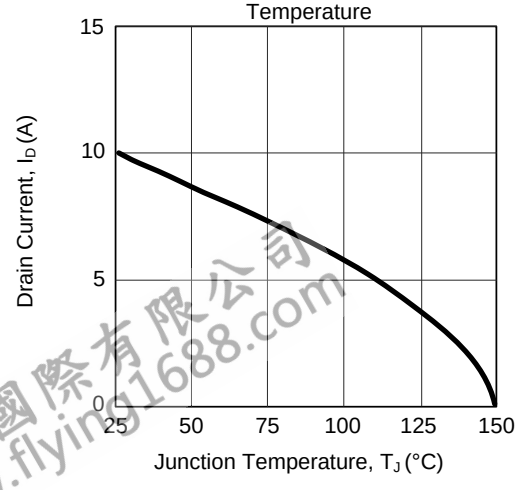
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)